

ABSTRACT OF THE DISCLOSURE

A carrier portion (15) carries a strip wafer (S) longitudinally in a carrying direction (16). A processing portion (17) applies local processing such as plasma etching, thermal oxidation, CVD processing, and exposure to a partial processing region 5 (18) of the main surface of the strip wafer (S). Uniformity in processing only has to be secured in the limited processing region (18). Since the processing region (18) moves on the strip wafer (S) when the strip wafer (S) is carried, the entire main surface of the strip wafer (S) is uniformly processed with ease. The length (L) of the strip wafer (S) is variable according to the expansion or reduction in the volume of production without any 10 modification in the processing portion (17). Thus, expansion or reduction in the volume of production of semiconductor devices of the same kind can be met at a low cost.